Ordering number:EN5063

FC155

PNP Epitaxial Planar Silicon Transistor (With bias resistances)
PNP Epitaxail Planar Silicon Transistor

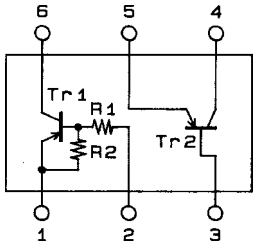
Constant-Current Circuit Applications

DISCONTINUED PRODUCT

Features

- Complex type of 2 devices (transistor with resistances and low saturation transistor) contained in one package, facilitating high-density mounting.

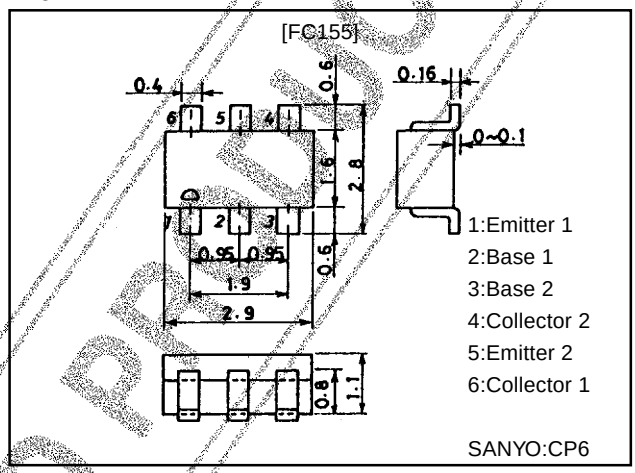
Electrical Connection



1:Emitter 1
2:Base 1
3:Base 2
4:Collector 2
5:Emitter 2
6:Collector 1

Package Dimensions

unit:mm
2104A



1:Emitter 1
2:Base 1
3:Base 2
4:Collector 2
5:Emitter 2
6:Collector 1

SANYO:CP6

Specifications

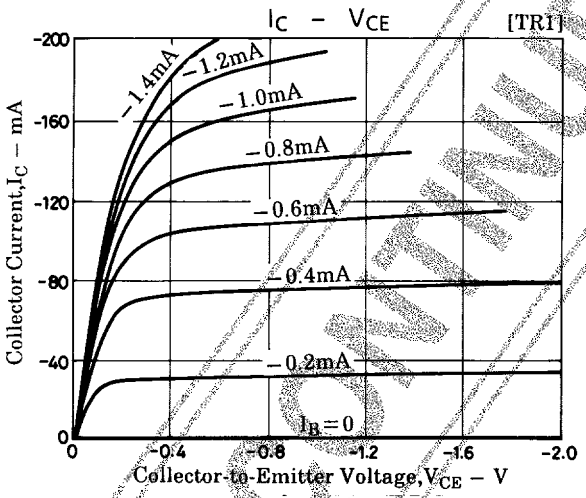
Absolute Maximum Ratings at Ta = 25˚C

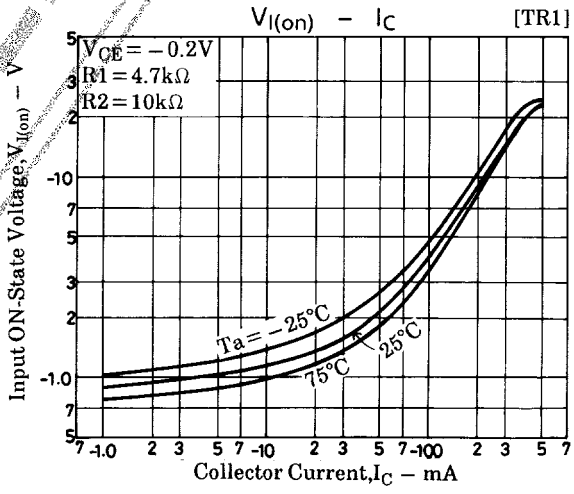
Parameter	Symbol	Conditions	Ratings	Unit
[TR1]				
Collector-to-Base Voltage	V_{CBO}		–20	V
Collector-to-Emitter Voltage	V_{CEO}		–15	V
Emitter-to-Base Voltage	V_{EBO}		–5	V
Collector Current	I_C		–500	mA
Collector Current (Pulse)	I_{CP}		–1	A
Base Current	I_B		–5	mA
Collector Dissipation	P_C	1 unit	200	mW
Total Dissipation	P_T		300	mW
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C
[TR2]				
Collector-to-Base Voltage	V_{CBO}		–20	V
Collector-to-Emitter Voltage	V_{CEO}		–15	V
Emitter-to-Base Voltage	V_{EBO}		–5	V
Collector Current	I_C		–500	mA
Collector Current (Pulse)	I_{CP}		–1	A
Base Current	I_B		–100	mA
Collector Dissipation	P_C	1 unit	200	mW
Total Dissipation	P_T		300	mW
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

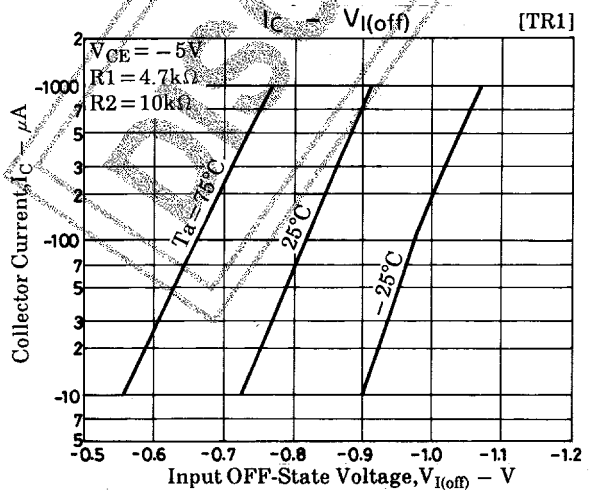
SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

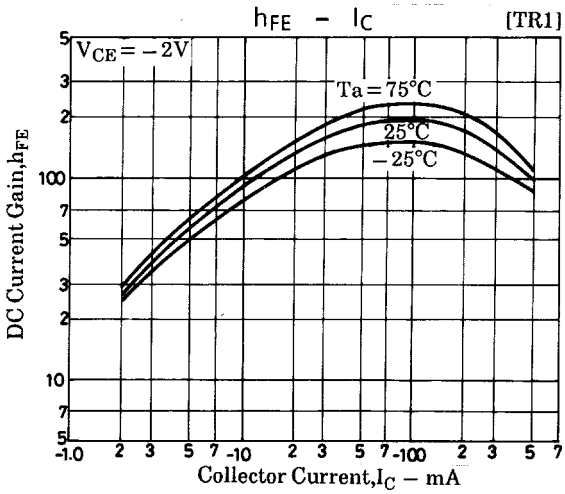
Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditons	Ratings			Unit
			min	typ	max	
[TR1]						
Collector Cutoff Current	I_{CBO}	V_{CB}=–15V, I_E=0			–0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=–4V, I_C=0	–210	–270	–390	μA
DC Current Gain	h_{FE}	V_{CE}=–2V, I_C=–100mA	100			
Gain-Bandwidth Product	f_T	V_{CE}=–2V, I_C=–50mA		150		MHz
Output Capacitance	Cob	V_{CE}=–10V, f=1MHz		5		pF
C-E Saturation Voltage	$V_{CE(sat)}$	I_C=–100mA, I_B=–5mA		–100	–250	mV
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C=–10μA, I_E=0	–20			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C=–1mA, R_{BE}=∞	–15			V
Input-OFF-State Voltage	$V_{I(off)}$	V_{CE}=–5V, I_C=–100μA	–0.7	–0.80	–0.95	V
Input-ON-State Voltage	$V_{I(on)}$	V_{CE}=–0.2V, I_C=–10mA	–0.85	–1.2	–1.8	V
Input Resistance	R1		3.3	4.7	6.1	V
Resistance Ratio	R1/R2			0.47		kΩ
[TR2]						
Collector Cutoff Current	I_{CBO}	V_{CB}=–15V, I_E=0			–0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=–4V, I_C=0			–0.1	μA
DC Current Gain	$h_{FE}(1)$	V_{CE}=–2V, I_C=–10mA	160		560	
	$h_{FE}(2)$	V_{CE}=–2V, I_C=–400mA	70			MHz
Gain-Bandwidth Product	f_T	V_{CE}=–2V, I_C=–50mA		400		pF
Output Capacitance	Cob	V_{CE}=–10V, f=1MHz		6.5		mV
C-E Saturation Voltage	$V_{CE(sat)}$	I_C=–200mA, I_B=–10mA		–200	–360	V
B-E Saturation Voltage	$V_{BE(sat)}$	I_C=–200mA, I_B=–10mA		–0.95	–1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C=–10μA, I_E=0	–20			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C=–1mA, R_{BE}=∞	–15			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	I_C=–10μA, I_C=0	–5			V









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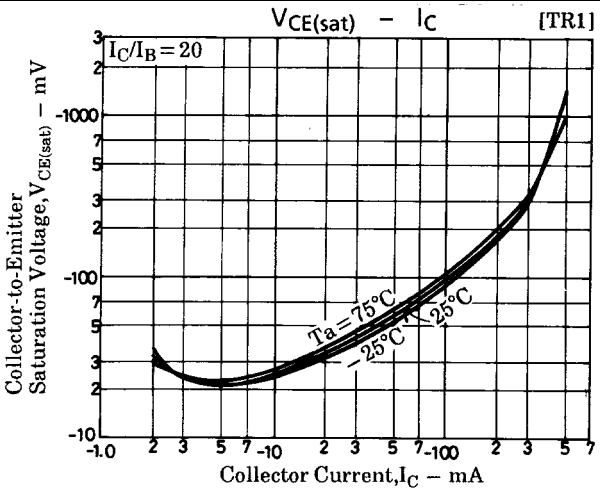

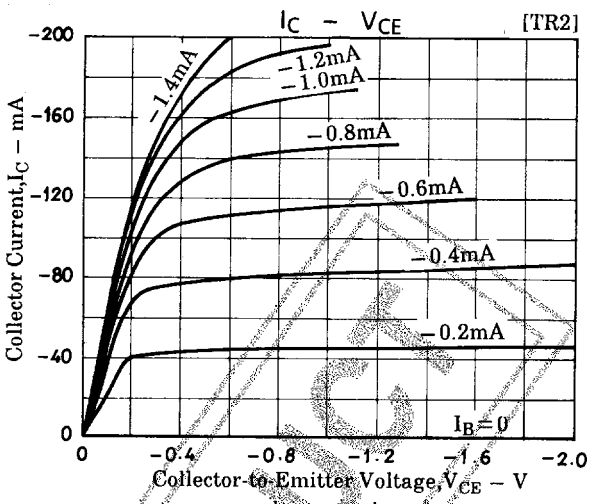

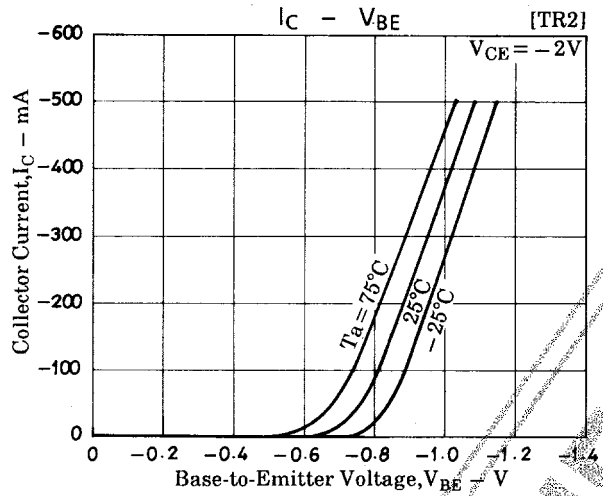

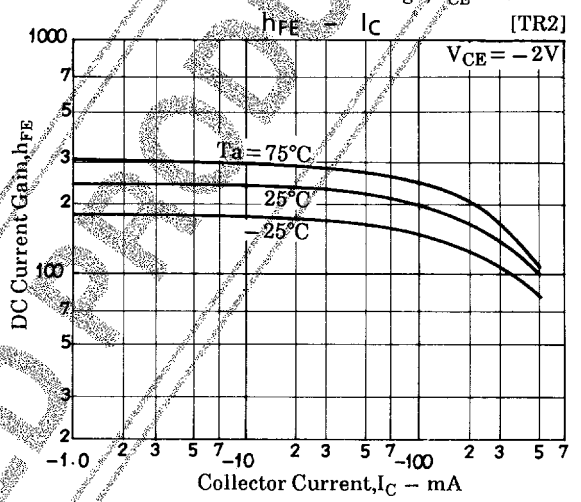

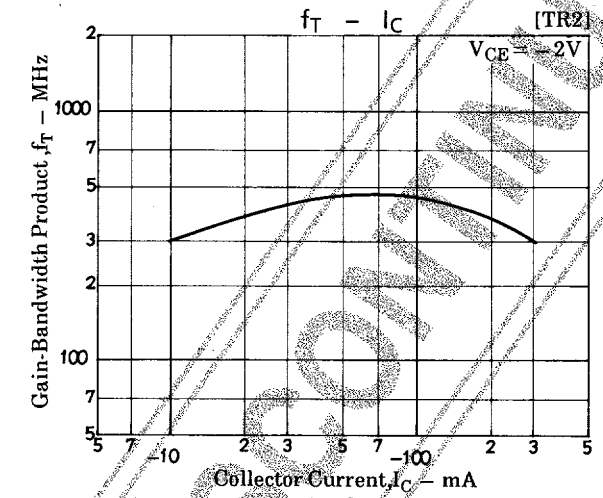

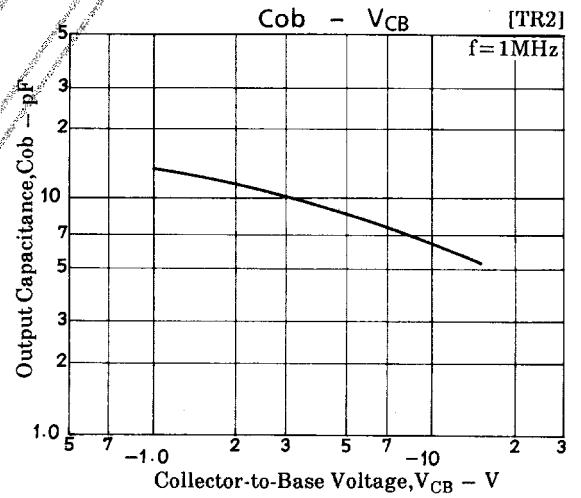

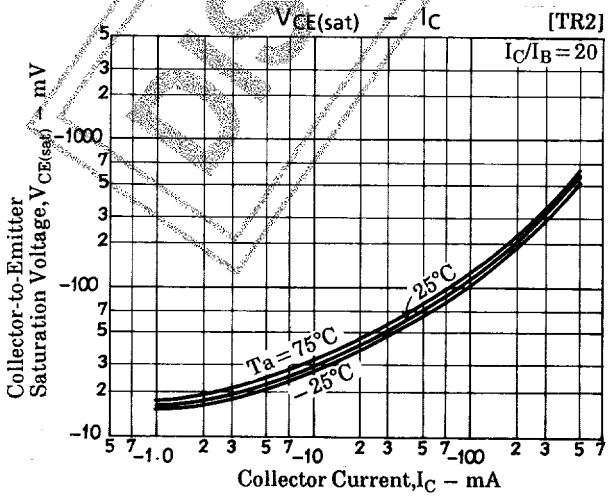

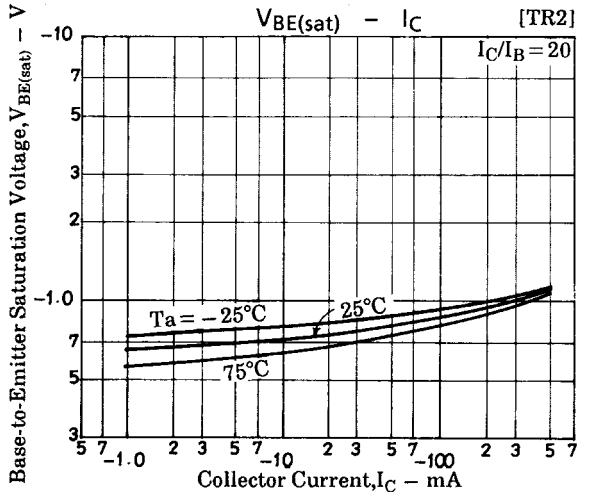

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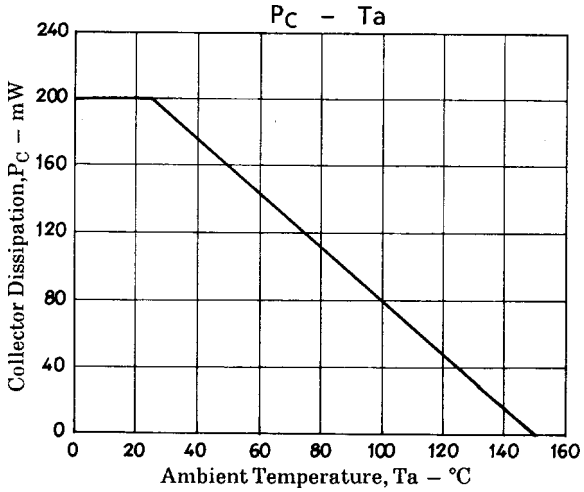

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